Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	12	(voltage adj supply adj circuit) and (voltage polarity adj inversion adj circuit) and (voltage adj protection adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:36
L2	0	(voltage adj supply adj circuit) and (voltage adj polarity adj inversion adj circuit) and (voltage adj protection adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:37
L4	0	(voltage adj supply adj circuit) and (polarity adj inversion adj circuit) and (voltage adj protection adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:37
L5	0	(voltage adj supply adj circuit) and (polarity adj inversion adj circuit) and (protection adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:37
L6	1	(supply adj circuit) and (polarity adj inversion adj circuit) and (protection adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:38
L7	24	(supply adj circuit) and (polarity adj inversion adj circuit) and (detection adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:44
L8	294	(memory adj cell adj array) and (voltage adj supply adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:45
L9	43	(memory adj cell adj array) and (voltage adj supply adj circuit) and (detection adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:48

L10	1	(memory adj cell adj array) and (voltage adj supply adj circuit) and (detection adj circuit) and (polarity adj inversion adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:46
L11	1150	257/390.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:48
L12	363	257/391.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:56
L13	806	257/202.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:54
L14	1	(inverting adj polarity adj voltage) and (detecting adj value adj voltage adj supplied)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:56
L15	1	(inverting adj polarity adj voltage) and (detecting adj value adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:56
L16	1	257/365.ccls. and polarity and inversion and detection and (memory adj array)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:35
L17	146	"365"/$.ccls. and polarity and inversion and detection and (memory adj array)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:36

L18	1966	257/316.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:35
L19	1496	365/185.18.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:37
L20	930	365/185.22.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:37
L21	695	365/185.28.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:38
L22	1248	365/185.33.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:38
L23	3664	365/200.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:38
L24	332	365/185.14.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:39
L25	264	365/185.16.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:39

S1	470	257/317.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:29
S2	8	tokui-kei.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 11:44
S3	1303	iwata-hiroshi.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 11:48
S4	5	iwata-hiroshi.inv. and (generating near voltage) and channel and source and spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 11:48
S5	35	yaoi-yoshifumi.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:05
S6	87	nawaki-masaru.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:10
S7	0	(semiconductor adj storage) and (voltage adj supply adj circuit) and (voltage polarity adj inversion adj circuit) and (voltage adj value adj protection adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:16
S8	0	(voltage adj supply adj circuit) and (voltage polarity adj inversion adj circuit) and (voltage adj value adj protection adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:16

S10	2	(voltage adj supply adj circuit) and (voltage adj polarity adj inversion adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:27
S11	12	(voltage adj polarity adj inversion adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:27
S12	335	retain adj electric adj charge	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:29
S13	0	(retain adj electric adj charge) near spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:30
S14	0	(retain adj electric adj charge) with spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:30
S15	6	(retain adj electric adj charge) same spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:31
S16	0	(store adj electric adj charge) near spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:31
S17	1	(store adj electric adj charge) with spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:31

S18	6	(store adj electric adj charge) same spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 12:38
S19	205	(storage) near spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 15:48
S20	344	(sin or (silicon adj nitride)) adj sidewall adj spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:33
S21	1580	(sin or (silicon adj nitride)) adj spacers	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:37
S22	0	((electric adj charge) or polarization) near (sidewall adj spacer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:38
S23	4	((electric adj charge) or polarization) with (sidewall adj spacer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:46
S24	0	"5780339".pn. and nonvolatile	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:46
S25	0	"5780339".pn. and (non adj volatile)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 17:26

| S26 | 4 | semi adj fusible adj link adj system | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/24 17:27 |